

**IN THE CLAIMS**

Claims 1-23 (Canceled)

24. (Currently Amended) A method of performing lithography on a substrate using a resist film,

said method comprising the following steps:

exposing said resist film with electrons from a tip held by a top of a spring by supplying a first-~~bias~~ voltage between said tip and said substrate for portions of said resist film in which latent images are formed, and

irradiating said resist film with electrons from said tip by supplying a second-~~bias~~ voltage between said tip and said substrate for portions of said resist film in which latent images are not formed,

wherein said first-~~bias~~ voltage is larger than said second-~~bias~~ voltage,

wherein said tip contacts with said resist film during said exposing step and during said irradiating step, and

wherein said second voltage is supplied so as not to form said latent images in said resist film.

25. (Canceled)

26. (Currently Amended) The method of claim ~~25~~ 24,  
wherein

said tip contacts with said resist film by a Coulomb  
force supplied from either of said first or second ~~bias~~  
voltage between said tip and said substrate.

27. (Canceled)

28. (Currently Amended) A fabrication apparatus,  
comprising,

an electrically conductive tip;

a first holder, which is used as a spring, for holding  
said tip;

a second holder for holding a substrate having a resist  
layer on a surface thereof;

a moving mechanism for said second holder; and

a device for supplying exposure current from said tip to  
said resist layer by supplying a voltage between said second  
holder and said tip, wherein

said first holder is deformed by a Coulomb force produced  
by said voltage, and

said substrate is relatively moved with said tip along an X-Y surface of said substrate while holding said tip in contact with said resist layer,

said device exposes said resist layer, while said tip is in contact with said resist layer, with electrons from said tip by supplying a first-~~bias~~ voltage between said tip and said substrate for portions of said resist layer in which latent images are formed<sub>7i</sub> and irradiates said resist layer, while said tip is in contact with said resist layer, with electrons from said tip by supplying a second-~~bias~~ voltage between said tip and said substrate for portions of said resist layer in which latent images are not formed, and where said first-~~bias~~ voltage is larger than said second ~~bias~~ voltage.